

NTP5864N

MOSFET – Power 60 V, 63 A, 12.4 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		V_{DSS}	60	V	
Gate-to-Source Voltage – Continuous		V_{GS}	± 20	V	
Gate-to-Source Voltage – Non-Repetitive ($t_p = 10 \mu\text{s}$)		V_{GS}	± 30	V	
Continuous Drain Current – $R_{\theta JC}$ (Note 1)	Steady State	I_D	$T_C = 25^\circ\text{C}$	63	A
			$T_C = 100^\circ\text{C}$	45	
Power Dissipation – $R_{\theta JC}$ (Note 1)	Steady State	P_D	$T_C = 25^\circ\text{C}$	107	W
			$T_C = 100^\circ\text{C}$	54	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	252	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode) Pulsed		I_S	63	A	
Single Pulse Drain-to-Source Avalanche Energy – ($L = 0.1 \text{ mH}$)		EAS	80	mJ	
		IAS	40	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Case (Drain) – Steady State (Note 1)	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	33	$^\circ\text{C/W}$

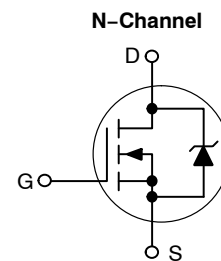
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).



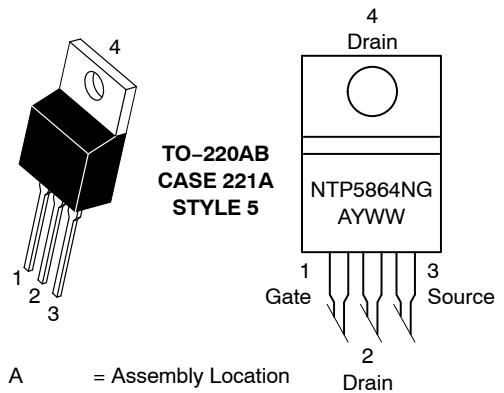
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$ (Note 1)
60 V	12.4 mΩ @ 10 V	63 A



MARKING DIAGRAM & PIN ASSIGNMENT



- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NTP5864NG	TO-220 (Pb-Free)	50 Units / Rail

NTP5864N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			58		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V, T _J = 25°C			1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		4.0	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-10		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		10.2	12.4	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 20 A		10		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		1680		pF
Output Capacitance	C _{OSS}			189		
Reverse Transfer Capacitance	C _{RSS}			124		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 48 V, I _D = 20 A		31		nC
Threshold Gate Charge	Q _{G(TH)}			2.0		
Gate-to-Source Charge	Q _{GS}			7.3		
Gate-to-Drain Charge	Q _{GD}			10		
Gate Resistance	R _g			0.5		Ω

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DD} = 48 V, I _D = 20 A, R _G = 2.5 Ω		10		ns
Rise Time	t _r			6.4		
Turn-Off Delay Time	t _{d(OFF)}			18		
Fall Time	t _f			4.6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 40 A	T _J = 25°C	0.94	1.2	V
			T _J = 125°C	0.84		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = 20 A		24		ns
Charge Time	t _a			16		
Discharge Time	t _b			7.9		
Reverse Recovery Charge	Q _{RR}			20		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

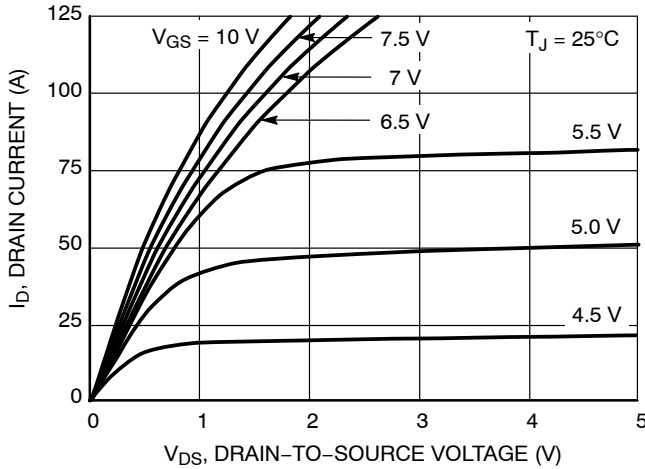


Figure 1. On-Region Characteristics

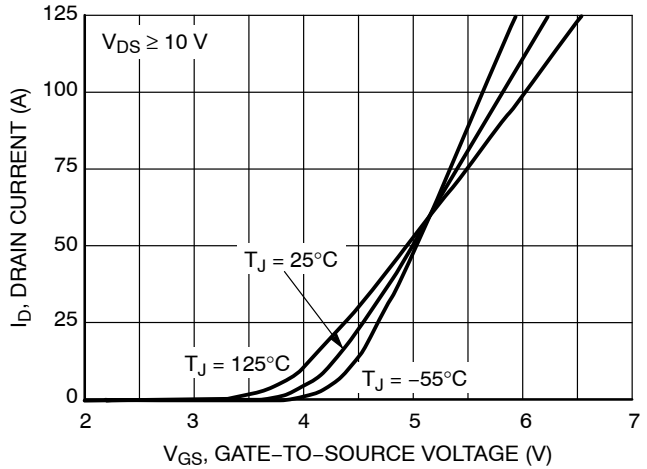


Figure 2. Transfer Characteristics

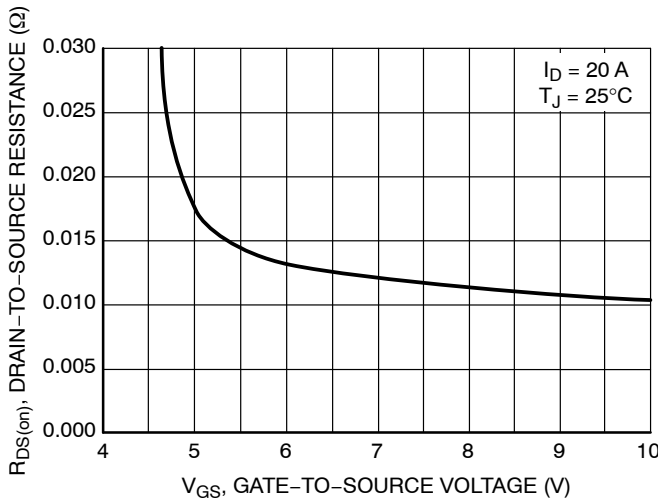


Figure 3. On-Resistance vs. Gate Voltage

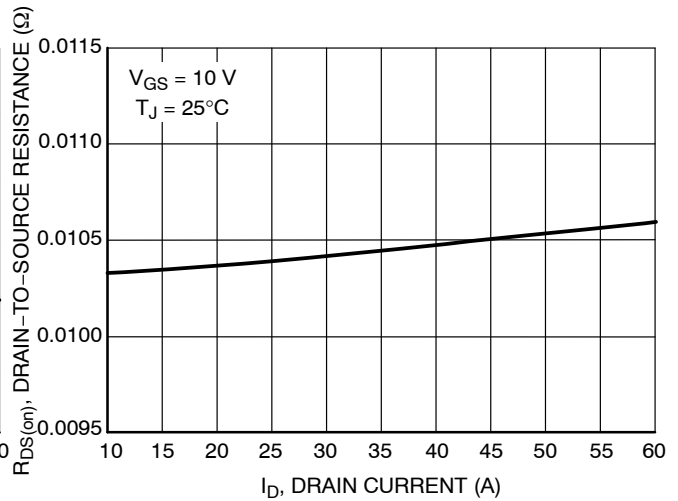


Figure 4. On-Resistance vs. Drain Current

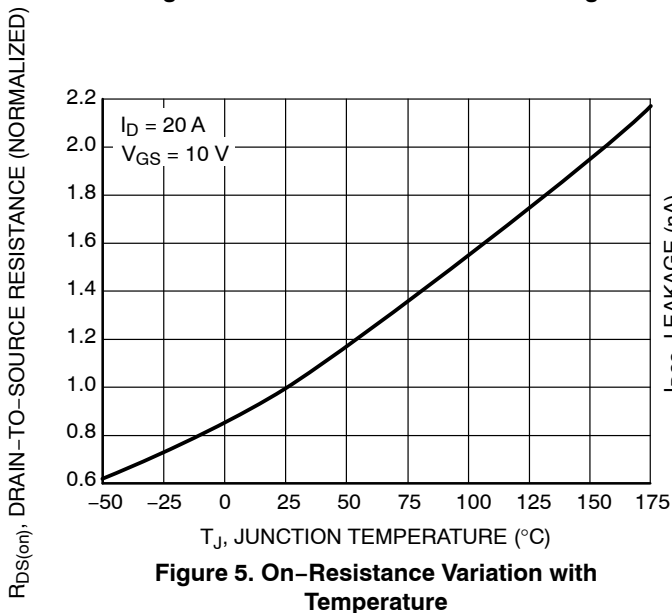


Figure 5. On-Resistance Variation with Temperature

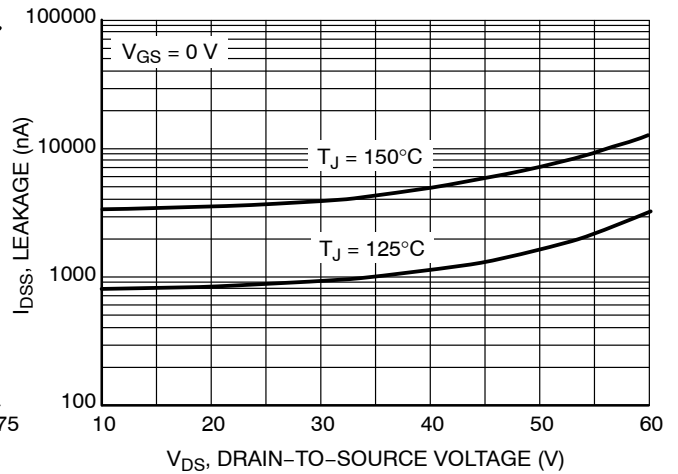


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTP5864N

TYPICAL CHARACTERISTICS

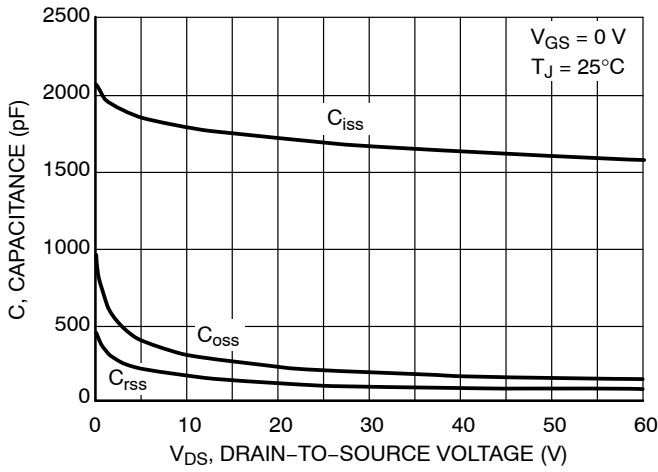


Figure 7. Capacitance Variation

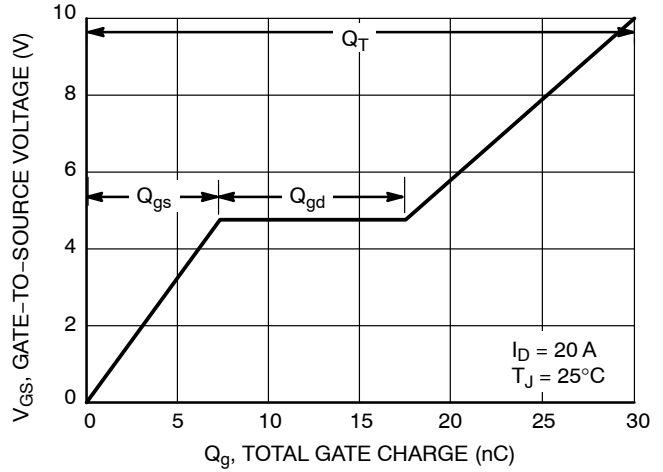


Figure 8. Gate-to-Source vs. Total Charge

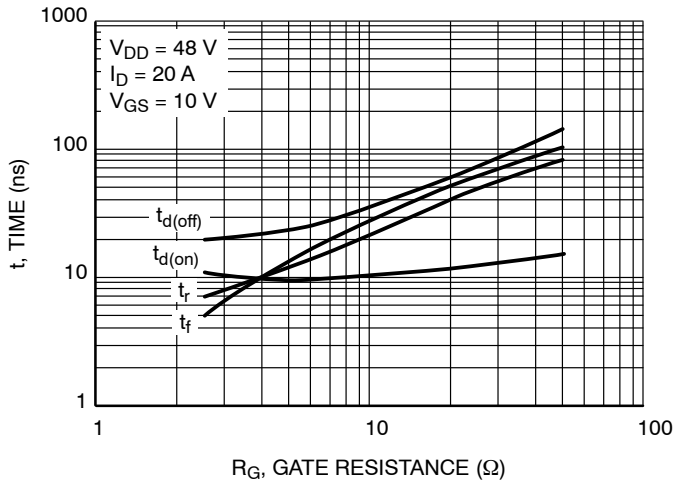


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

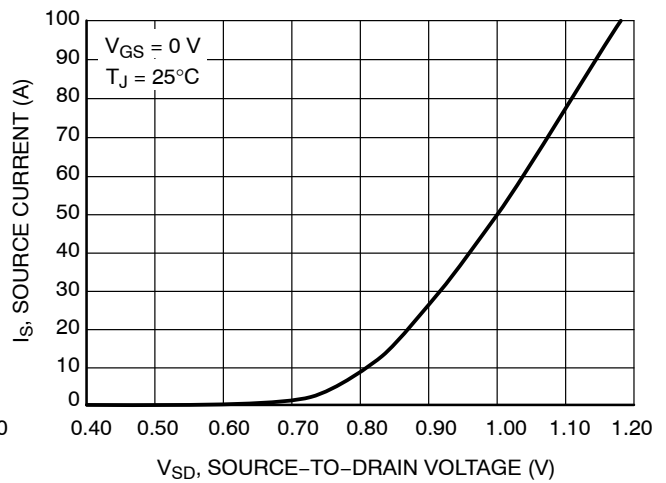


Figure 10. Diode Forward Voltage vs. Current

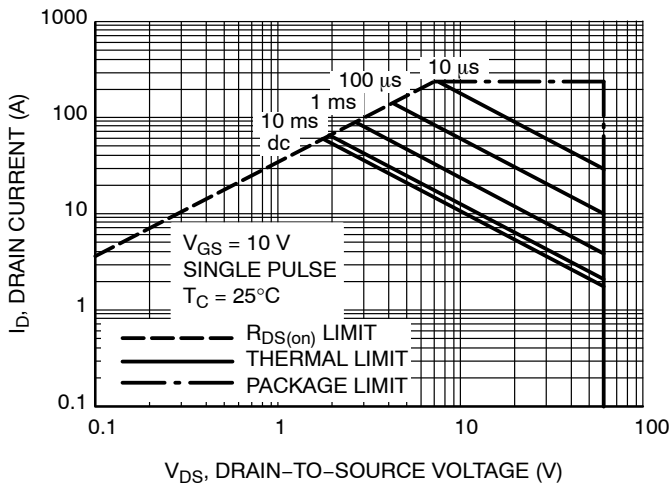


Figure 11. Maximum Rated Forward Biased Safe Operating Area

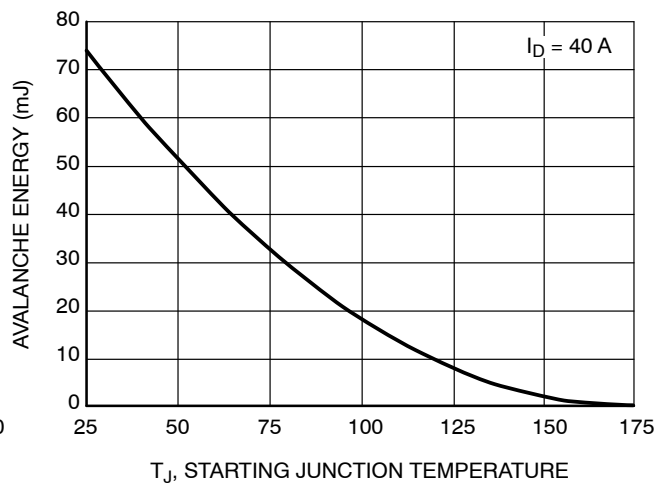


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

NTP5864N

TYPICAL CHARACTERISTICS

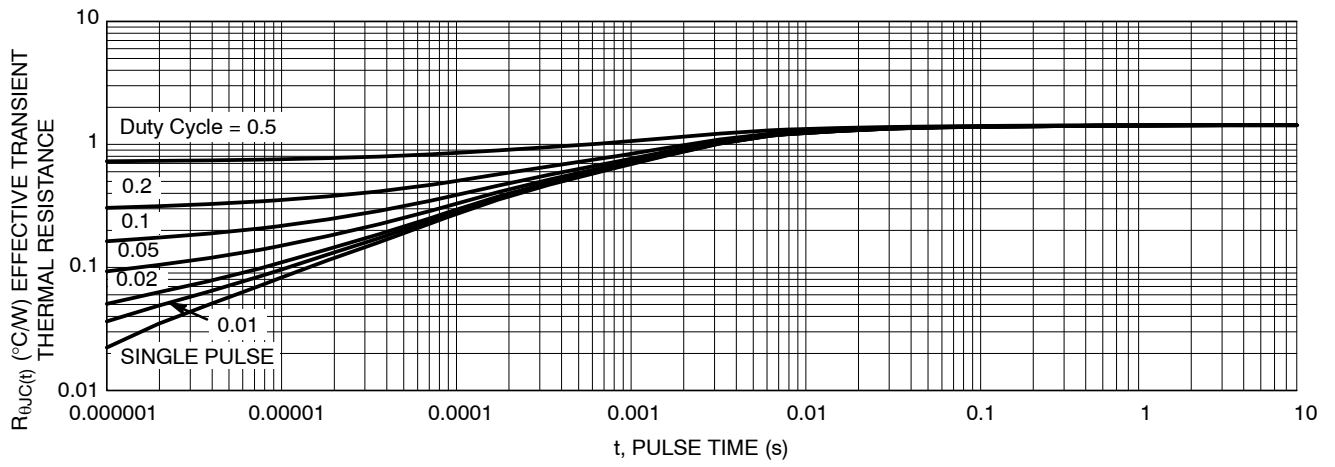


Figure 13. Thermal Response

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